

148914

SEARCH REQUEST FORM Scientific and Technical Information Center - EIC2800

Rev. 3/15/2004 This is an experimental format -- Please give suggestions or comments to Jeff Harrison, JEF-4B68, 272-2511.

Date 3/24/05 Serial # 101657,069 Priority Application Date 6/21/01Your Name M. Harrison Examiner # _____AU 2822 Phone 202-1838 Room 5A30In what format would you like your results? Paper is the default. ☒ PAPER ☐ DISK ☐ EMAILIf submitting more than one search, please prioritize in order of need. *need before 4/2*

The EIC searcher normally will contact you before beginning a prior art search. If you would like to sit with a searcher for an interactive search, please notify one of the searchers.

Where have you searched so far on this case?

Circle: ☐ USPT ☐ DWPI ☐ EPO Abs ☐ JPO Abs ☐ IBM TDB

Other: _____

What relevant art have you found so far? Please attach pertinent citations or Information Disclosure Statements. _____

What types of references would you like? Please checkmark:

Primary Refs ☒ Nonpatent Literature _____ Other _____Secondary Refs ☒ Foreign Patents _____

Teaching Refs _____

What is the topic, such as the **novelty**, motivation, utility, or other specific facets defining the desired **focus** of this search? Please include the concepts, synonyms, keywords, acronyms, registry numbers, definitions, structures, strategies, and anything else that helps to describe the topic. Please attach a copy of the abstract and pertinent claims.Claims 55 + 56Problem: see paragraphs 2-6
Solution: " " 7Rhodium Film

Staff Use Only

Searcher: HarrisonSearcher Phone: 22511Searcher Location: STIC-EIC2800, JEF-4B68Date Searcher Picked Up: 4-11-05Date Completed: 72

Searcher Prep/Rev Time: _____

Online Time: 4.3

Type of Search

Structure (#) _____

Bibliographic ☒ _____

Litigation _____

Fulltext _____

Patent Family _____

Other _____

Vendors

STN ☒ _____

Questel/Orbit _____

Lexis-Nexis _____

WWW/Internet _____

Other _____

CAS/STN FILE 'REGISTRY' ENTERED AT 16:33:42 ON 11 APR 2005

L1 54 S RH >99/MAC
 L2 1 S RHODIUM/CN

FILE 'HCAPLUS' ENTERED AT 16:34:36 ON 11 APR 2005

E CAPACITORS/CT
 L3 135433 S (CAPACITORS/CT OR "ELECTRIC CAPACITORS"/CT
 OR "ELECTRIC CONDENSERS"/CT OR "CONDENSERS (ELECTRIC)"/CT OR
 "ELEC. CAPACITORS"/CT OR "ELEC. CONDENSERS"/CT OR "CAPACITOR
 ELECTRODES"/CT) OR ("CERAMIC CAPACITORS"/CT OR "ELECTRIC
 CAPACITORS (L) CERAMIC, MULTILAYER"/CT OR "ELECTRIC CAPACITORS
 (L) CERAMIC, SEMICONDUCTIVE"/CT OR "ELECTRIC CAPACITORS (L)
 CERAMIC"/CT OR "ELECTRIC CAPACITORS (L) DOUBLE-LAYER"/CT OR
 "ELECTRIC CAPACITORS (L) ELECTRODES"/CT OR "ELECTRIC CAPACITORS
 (L) ELECTROLYTIC"/CT OR "ELECTRIC CAPACITORS (L) FILM"/CT OR
 "ELECTRIC CAPACITORS (L) MULTILAYER"/CT OR "ELECTRIC CAPACITORS
 (L) SEMICONDUCTIVE"/CT OR "ELECTRIC CAPACITORS (L) SUPERCONDUCTIVE"/CT OR "ELECTRIC CAPACITORS (L) THICK-FILM"/CT OR
 "ELECTRIC CAPACITORS (L) VARACTORS"/CT OR "ELECTROLYTIC
 CAPACITORS"/CT OR "ELECTRIC CAPACITORS (L) ELECTROLYTIC,
 ANODES"/CT OR "ELECTRIC CAPACITORS (L) ELECTROLYTIC, CATHODES"/
 CT OR "ELECTRIC CAPACITORS (L) ELECTROLYTIC, ELECTRODES"/CT OR
 "ELECTRIC CAPACITORS (L) ELECTROLYTIC, SOLID"/CT OR "FERROELECTRIC
 CAPACITORS"/CT OR "MIM CAPACITORS"/CT OR "MOS CAPACITORS"/CT
 OR VARACTORS/CT OR ELECTRETS/CT OR "ELECTRIC BREAKDOWN"/CT
 OR "ELECTRIC CHARGE"/CT) OR CAPACITOR OR (PLATE OR LAYER OR
 FILM OR LAMINA#####) (1A)ELECTRODE
 L4 510 S (L3 OR CAPACITOR OR ELECTRIC####(3A) (CONDEN
 SOR OR CONDENSER) OR CAPACIT####(2A) (ELEMENT OR DEVICE)) AND
 (L1 OR L2 OR (RH OR RHODIUM) (1A) (ELEMENTAL OR METAL))
 E ATOMIC LAYER DEPOSITION/CT
 L5 9 S L4 AND (ALD OR ALE OR ATOMIC LAYER OR
 "ATOMIC LAYER EPITAXY"/CT OR ATOM####(2A)BEAM)
 L6 1235 S (L1 OR L2) (L) (ELECTRODE OR CONDUCTOR)
 L7 127 S (L1 OR L2) (L) ELECTRIC#### AND (L1 OR L2) (L) CONTACT###
 L8 2 S (L6 OR L7) AND (ALD OR ALE OR ATOMIC LAYER
 OR "ATOMIC LAYER EPITAXY"/CT OR ATOM####(2A)BEAM)
 L9 0 S L8 NOT L5

CAS/STN FILE 'INSPEC' ENTERED AT 08:09:59 ON 12 APR 2005

L1 4534 S (RH/CHI OR "RH ADS"/CHI OR "RH BIN"/CHI OR
"RH DOP"/CHI OR "RH EL"/CHI OR "RH INT"/CHI OR "RH SS"/CHI OR "RH SUR"/CHI)
E ATOMIC LAYER DEPOSITION/CT

L2 6614 S "ATOMIC LAYER DEPOSITION"/CT OR "ATOMIC LAYER EPITAXIAL GROWTH"/CT OR
ALE OR ALD OR ATOMIC LAYER

L3 25 S L1 AND L2
E CAPACITORS/CT

L4 89311 S ("DIELECTRIC DEVICES"/CT OR "ELECTROSTATIC DEVICES"/CT OR "REACTORS (ELECTRIC)"/CT
OR CAPACITORS/CT OR "CAPACITOR TESTING"/CT OR "CONDENSERS (ELECTRIC)"/CT OR "ELECTRIC CONDENSERS"/CT OR
"CERAMIC CAPACITORS"/CT OR "ELECTROLYTIC CAPACITORS"/CT OR SUPERCAPACITORS/CT OR "FERROELECTRIC
CAPACITORS"/CT OR "MIS CAPACITORS"/CT OR "MOS CAPACITORS"/CT OR "POWER CAPACITORS"/CT OR "CAPACITOR
SWITCHING"/CT OR SUPERCAPACITORS/CT OR "THICK FILM CAPACITORS"/CT OR "THIN FILM CAPACITORS"/CT OR
VARACTORS/CT OR CAPACITANCE/CT OR "CAPACITANCE MEASUREMENT"/CT OR "CAPACITOR STORAGE"/CT OR ELECTRETS/CT
OR "ELECTRIC CHARGE"/CT OR MICA/CT OR Q-FACTOR/CT OR B2130/CT OR "CERAMIC CAPACITORS"/CT OR "ELECTRIC
DOUBLE LAYER CAPACITORS"/CT OR "ELECTRICAL DOUBLE LAYER CAPACITORS"/CT OR "ELECTROLYTIC CAPACITORS"/CT
OR "FERROELECTRIC CAPACITORS"/CT OR "METAL-INSULATOR-SEMICONDUCTOR CAPACITORS"/CT OR "METAL-OXIDE-
SEMICONDUCTOR CAPACITORS"/CT OR "MIS CAPACITORS"/CT OR "MLC CAPACITORS"/CT OR "MOS CAPACITORS"/CT OR
"MULTILAYER CERAMIC CAPACITORS"/CT OR "POWER CAPACITORS"/CT OR "TANTALUM ELECTROLYTIC CAPACITORS"/CT OR
"THICK FILM CAPACITORS"/CT OR "THIN FILM CAPACITORS"/CT) OR CAPACITOR OR CONDENSOR OR CONDENSER

L5 0 S L4 AND L3

L6 0 S ELECTRODE AND L3

L7 20 S L1 AND L4

L8 1 S (L3 OR L7) AND (RH OR RHODIUM) (2A) (ELEMENTAL OR METAL####)

L9 2126 S RHODIUM/CT

L10 240 S (RH OR RHODIUM) (1A) (ELEMENTAL OR METAL####)

L11 5200 S L1 OR L9 OR L10

L12 26 S L2 AND L11

L13 21 S L4 AND L11

L14 0 S L12 AND L13

L15 46 S (L12 OR L13) NOT L8

L16 14 S L15 AND (ELECTRODE OR CONDUCTOR)

E TEMP/PHP

L17 13 S TEMPERATURE/PHP AND L15

L18 21 S L16 OR L17

FILE 'METADEX' ENTERED AT 08:20:14 ON 12 APR 2005

L19 105 S (RH OR RHODIUM) (3A) ELECTRODE

L20 28 S (RH OR RHODIUM) (3A) CONDUCT#####

L21 89 S (RH OR RHODIUM) (3A) ELECTRIC#####

L22 0 S (RH OR RHODIUM) AND CAPACITOR

L23 1 S L20 AND L21

L24 1 S L19 AND L20

L25 2 S L19 AND L21

L26 3 S (L24 OR L25) NOT L23

FILE 'SCISEARCH' ENTERED AT 08:24:08 ON 12 APR 2005

L27 3 S ("ZHALKOTITARENKO A V, 1989, V11, P23,
METALLOFIZIKA"/RE OR "ZHALKOTITARENKO A V, 1989, V11, P25, METALLOFIZIKA"/RE)

FILE 'METADEX' ENTERED AT 08:25:36 ON 12 APR 2005

L28 3685 S ELECTRIC#### CONTACT#

L29 5 S (L19 OR L20 OR L21 OR L22) AND L28

L30 4 S L29 NOT (L23 OR L24 OR L25)

FILE 'INSPEC, COMPENDEX, JICST-EPLUS, PASCAL, HCAPLUS' ENTERED

L31 89 S CONTACT RESISTANCE CHARACTERISTICS/TI

L32 11 S L31 AND (RH OR RHODIUM)

L33 4 DUP REM L32 (7 DUPLICATES REMOVED)

L34 5208 S (RH OR RHODIUM) (3A) (CONDUCTOR OR PLATE OR ELECTRODE OR FILM OR LAYER)

L35 165 S CAPACITOR AND L34

L36 1115 S (RH OR RHODIUM) (3A) PLAT###

L37 11 S CAPACITOR AND L36

L38 71 S (ALD OR ALE OR ATOMIC LAYER) AND L34

L39 2 S (ALD OR ALE OR ATOMIC LAYER) AND L36

L40 4 S (ALD OR ALE OR ATOMIC LAYER) AND L35

L41 4 S L38 AND ELECTRODE

L42 17 S L37 OR (L39 OR L40 OR L41)

L43 17 DUP REM L42 (0 DUPLICATES REMOVED)

L44 17 S L43 NOT L33